

**METHOD FOR INTEGRATION OF SILICIDE CONTACTS
AND SILICIDE GATE METALS**

ABSTRACT OF THE DISCLOSURE

A CMOS silicide metal integration scheme that allows for the incorporation of silicide contacts (S/D and gates) and metal silicide gates using a self-aligned process (salicide) as well as one or more lithography steps is provided. The integration scheme of the present invention minimizes the complexity and cost associated in fabricating a CMOS structure containing silicide contacts and silicide gate metals.